

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,821,829 B1
APPLICATION NO. : 09/592349
DATED : November 23, 2004
INVENTOR(S) : William C. Peatman

Page 1 of 1

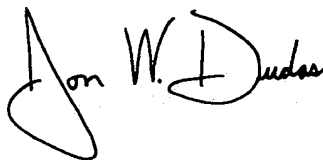
It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 8, After Line 36, Claim No. 11:

Insert --forming a dielectric layer over the gate contact, the remaining first portion of the undoped gallium arsenide capping layer and the exposed portion of the surface of the delta-doped heteroepitoxial semiconductor substrate;--

Signed and Sealed this

Twenty-sixth Day of December, 2006

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a cursive "Dudas".

JON W. DUDAS
Director of the United States Patent and Trademark Office